

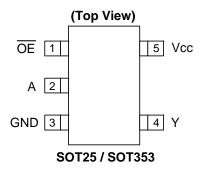
#### **Description**

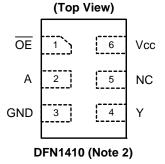
The 74LVCE1G125 is a single non-inverting buffer/bus driver with a 3-state output. The output enters a high impedance state when a HIGH-level is applied to the output en able (OE) pin. The device is designed for operation with a power supply range of 1.4V to 5.5V. The inputs are tholerant to 5.5 Vallowing this device to be usined in a minimized violating environment. The device is full by specified for partial power down applications using I OFF. The I OFF circuitry disables the output preventing damaging current backflow when the device is powered down.

#### **Features**

- Extended Supply Voltage Range from 1.4 to 5.5V
- Switching speed characterized for operation at 1.5V
- Offers 30% speed improvement over LVC at 1.8V.
- ± 24mA Output Drive at 3.3V
- CMOS low power consumption
- IOFF Supports Partial-Power-Down Mode Operation
- Inputs accept up to 5.5V
- ESD Protection Tested per JESD 22
   Exceeds 200-V Machine Model (A115-A)
   Exceeds 2000-V Human Body Model (A114-A)
- Latch-Up Exceeds 100mA per JESD 78, Class II
- Range of Package Options
- · Direct Interface with TTL Levels
- SOT25, SOT353 and DFN1410: Assembled with "Green" Molding Compound (no Br, Sb)
- Lead Free Finish/ RoHS Compliant (Note 1)

#### **Pin Assignments**





#### **Applications**

- · Voltag e Level Shifting
- · Bus Driver / Repeater
- Power Down Signal Isolation
- · General Purpose Logic
- Wide array of products such as.
  - PCs, networking, notebooks, netbooks, PDAs
  - Computer peripherals, hard drives, CD/DVD ROM
  - o TV, DVD, DVR, set top box
  - o Cell Phones, Personal Navigation / GPS
  - o MP3 players ,Cameras, Video Recorders

Notes: 1. EU Directive 2002/95/EC (RoHS). All applicable RoHS exemptions applied. Please visit our website at http://www.diodes.com/products/lead\_free.html.

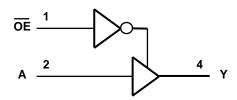
2. Pin 2 and pin 5 of the DFN1410 package are internally connected.



# **Pin Descriptions**

Pin Name	Description			
OE Output Enable (active low)				
A Data Input				
GND	Ground			
Y	Data Output			
Vcc	Supply Voltage			

# **Logic Diagram**



## **Function Table**

Inp	uts	Output		
ŌĒ	ŌE A			
L	Н	Н		
L	L	L		
Н	Х	Z		



## **Absolute Maximum Ratings (Note 3)**

Symbol	Description	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	KV
ESD MM	Machine Model ESD Protection	200	V
V <sub>cc</sub>	Supply Voltage Range	-0.5 to 6.5	V
Vı	Input Voltage Range	-0.5 to 6.5	V
Vo	Voltage applied to output in high impedance or I <sub>OFF</sub> state	-0.5 to 6.5	V
V <sub>o</sub>	Voltage applied to output in high or low state	-0.3 to V <sub>CC</sub> +0.5	V
I <sub>IK</sub>	Input Clamp Current V <sub>I</sub> <0 -50		mA
I <sub>OK</sub>	Output Clamp Current	-50	mA
Io	Continuous output current	±50	mA
	Continuous current through Vdd or GND	±100	mA
TJ	Operating Junction Temperature	-40 to 150	°C
T <sub>STG</sub>	Storage Temperature	-65 to 150	°C

Note: 3. Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.



# **Recommended Operating Conditions (Note 4)**

Symbol		Parameter	Min	Max	Unit	
V	On anating Valtage	Operating	1.4	5.5	V	
$V_{CC}$	Operating Voltage	Data retention only	1.2		V	
		V <sub>CC</sub> = 1.4 V to 1.95 V	0.65 X V <sub>CC</sub>			
\/	High-level Input Voltage	V <sub>CC</sub> = 2.3 V to 2.7 V	1.7		V	
$V_{IH}$		V <sub>CC</sub> = 3 V to 3.6 V	2		V	
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	0.7 X V <sub>CC</sub>			
		V <sub>CC</sub> = 1.4 V to 1.95 V		0.35 X V <sub>CC</sub>		
V	Low lovel input voltage	V <sub>CC</sub> = 2.3 V to 2.7 V		0.7	V	
$V_{IL}$	Low-level input voltage	V <sub>CC</sub> = 3 V to 3.6 V		0.8	V	
		V <sub>CC</sub> = 4.5 V to 5.5 V		0.3 X V <sub>CC</sub>		
Vı	Input Voltage		0	5.5	V	
Vo	Output Voltage		0	V <sub>CC</sub>	V	
	High-level output current	Vcc=1.4 V		-3		
		V <sub>CC</sub> = 1.65 V		-4	m ^	
		V <sub>CC</sub> = 2.3 V		-8		
I <sub>OH</sub>			-16		mA	
		$V_{CC} = 3 V$		-24		
		V <sub>CC</sub> = 4.5 V		-32		
		Vcc=1.4 V		3		
		V <sub>CC</sub> = 1.65 V		4		
	La la da ta ta mad	V <sub>CC</sub> = 2.3 V		8	mΑ	
I <sub>OL</sub>	Low-level output current		16			
		$V_{CC} = 3 V$		24		
		V <sub>CC</sub> = 4.5 V		32		
		V <sub>CC</sub> = 1.4 to 3V	20			
$\Delta t/\Delta V$	Input transition rise or fall rate	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$		10	ns/V	
		$V_{CC} = 5 \text{ V} \pm 0.5 \text{ V}$		5		
T <sub>A</sub>	Operating free-air temperature		-40 85		°C	

Note: 4. Unused inputs should be held at Vcc or Ground.



### Electrical Characteristics (All typical values are at Vcc = 3.3V, T<sub>A</sub> = 25°C)

Over recommended free-air temperature range (unless otherwise noted)

Symbol	Parameter	Test Conditions	Vcc	Min	Тур.	Max	Unit	
		$I_{OH} = -100 \mu A$	1.4 V to 5.5V	V <sub>CC</sub> - 0.1				
		$I_{OH} = -3mA$	1.4 V	1.05				
		$I_{OH} = -4mA$	1.65 V	1.2				
$V_{OH}$	High Level Output Voltage	$I_{OH} = -8mA$	2.3V	1.9			V	
	Voltage	I <sub>OH</sub> = -16mA	2.1/	2.4				
		I <sub>OH</sub> = -24mA	3 V	2.3				
		$I_{OH} = -32mA$	4.5 V	3.8				
		I <sub>OL</sub> = 100μA	1.4 V to 5.5V			0.1		
		I <sub>OL</sub> = 3mA	1.4V			.4		
		I <sub>OL</sub> = 4mA	1.65 V			0.45		
$V_{OL}$	High-level Input Voltage	I <sub>OL</sub> = 8mA	2.3V			0.3	V	
		I <sub>OL</sub> = 16mA	2.1/			0.4		
		$I_{OL} = 24mA$	3 V			0.55		
		$I_{OL} = 32mA$	4.5			0.55		
I <sub>I</sub>	Input Current	$V_I = 5.5 \text{ V or GND}$	0 to 5.5 V			± 5	μΑ	
I <sub>OFF</sub>	Power Down Leakage Current	$V_1$ or $V_0 = 5.5V$	0			± 10	μA	
l <sub>OZ</sub>	Z State Leakage Current	V <sub>O</sub> =0 to 5.5V	3.6V			10	μΑ	
I <sub>CC</sub> Sup	pply Current	$V_1 = 5.5V$ of GND $I_0=0$	1.4 V to 5.5V			10	μΑ	
$\Delta I_{CC}$	Additional Supply Current	One input at V <sub>CC</sub> – 0.6 V Other inputs at V <sub>CC</sub> or GND	3 V to 5.5V			500	μA	
C <sub>i</sub> Inpi	ıt Capacitance	$V_i = V_{CC} - \text{ or GND}$	3.3		3.5		pF	
	The second Decision	SOT25 (Note	5)		204			
$\theta_{JA}$	Thermal Resistance Junction-to-Ambient	SOT353 (Note	5)		371		°C/W	
	JOHN CHOIT-LO-AITIDIGITE	DFN1410 (Note	5)		430		]	
		SOT25 (Note	5)		52			
$\theta_{JC}$	Thermal Resistance Junction-to-Case	SOT353	(Note 5)		143		°C/W	
	Julionolion-10-0ase	DFN1410 (Note	5)		190			

Note: 5. Test condition for SOT25, SOT353 and DFN1410: Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.



## **Switching Characteristics**

Over recommended free-air temperature range, CL = 15pF (see Figure 1)

Parameter	Parameter From		Vcc = 1.5 V Vcc = ± 0.1V ± 0.7				Vcc = 3.3 V ± 0.3V		Vcc = 5 V ± 0.5V		Unit		
	(Input)	(OUTPUT)	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
t <sub>pd</sub>	Α	Y	1.9	6.9	1.3	4.8	0.5	3.6	0.4	3	0.4	3	ns

Over recommended free-air temperature range, CL = 30 or 50pF as noted (see Figure 2)

Parameter	From	то	Vcc = ± 0			: 1.8 V .15V		2.5 V 0.2V		3.3 V 3.3 V	Vcc :	= 5 V .5V	Unit
	(Input)	(OUTPUT)	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	O.I.I.
t <sub>pd</sub>	Α	Y	2.8	9	1.9	6.3	0.9	4.4	0.8	3.6	0.9	3.6	ns
t <sub>en</sub>	OE	Υ	3.3	10.1	2.3	7	1.2 5	.2	0.8 4	.3 0.9 4	.5		
t <sub>dis</sub> OE		Υ	1.3	9.2	0.9	6.4	0.8	4	0.8 4	.1 0.9 3	.7		

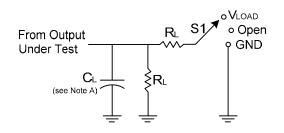
# **Operating Characteristics**

 $T_A = 25$  °C

	Parameter		Test		Vcc = 1.8 V	Vcc = 2.5 V	Vcc = 3.3 V	Vcc = 5 V	Unit	
			Conditions	TYP	TYP	TYP	TYP	TYP		
	C	Power dissipation	Outputs enabled	f 10 MH=	20 20	20	21		22	۲
	$C_{pd}$	capacitance	Outputs disabled	f = 10 MHz	2	2	2	2	4	pF

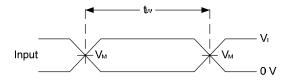


#### **Parameter Measurement Information**

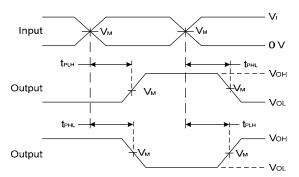


TEST	S1
t <sub>PLH</sub> /t <sub>PHL</sub>	Open
$t_{PLZ}/t_{PZL}$	Vload
t <sub>PHZ</sub> /t <sub>PZH</sub>	GND

Vcc	Inj	puts	V		Б
VCC	Vı	t <sub>r</sub> /t <sub>f</sub>	V <sub>M</sub>	CL	RL
1.5V±0.1V V	СС	≤2ns V	<sub>cc</sub> /2 15pF		1ΜΩ
1.8V±0.15V V	СС	≤2ns V	<sub>cc</sub> /2 15pF		1ΜΩ
2.5V±0.2V V	СС	≤2ns V	<sub>cc</sub> /2 15pF		1ΜΩ
3.3V±0.3V 3V		≤2.5ns 1.5V		15pF	1ΜΩ
5V±0.5V V	СС	≤2.5ns V	<sub>cc</sub> /2 15pF		1ΜΩ



#### **Voltage Waveform Pulse Duration**



Voltage Waveform Propagation Delay Times Inverting and Non Inverting Outputs

Output Control

Output Waveform 1
S1 at  $V_{\text{LOAD}}$ (see Note B)

Output Waveform 2
S1 at GND
(see Note B)  $V_{\text{M}}$   $V_{\text{M}}$   $V_{\text{M}}$   $V_{\text{M}}$   $V_{\text{M}}$   $V_{\text{M}}$   $V_{\text{M}}$   $V_{\text{M}}$   $V_{\text{M}}$   $V_{\text{LOAD}}$   $V_{\text{LOAD}}$   $V_{\text{LOAD}}$   $V_{\text{LOAD}}$   $V_{\text{CAD}}$   $V_{\text{CAD}}$ 

Voltage Waveform Enable and Disable Times
Low and High Level Enabling

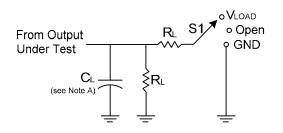
Notes: A. Includes test lead and test apparatus capacitance.

- B. All pulses are supplied at pulse repetition rate ≤ 10 MHz.
- C. Inputs are measured separately one transition per measurement.
- D. t<sub>PLZ</sub> and t<sub>PHZ</sub> are the same as t<sub>dis.</sub>
- E.  $t_{\text{PZL}}$  and  $t_{\text{PZH}}$  are the same as  $t_{\text{EN}}$ .
- F. t<sub>PLH</sub> and t<sub>PHL</sub> are the same as t<sub>PD</sub>.

Figure 1. Load Circuit and Voltage Waveforms

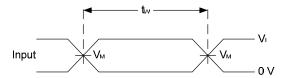


### **Parameter Measurement Information (Continued)**

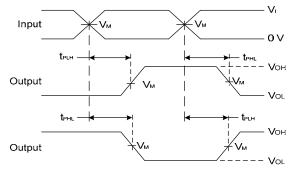


TEST	S1
t <sub>PLH</sub> /t <sub>PHL</sub>	Open
$t_{PLZ}/t_{PZL}$	Vload
t <sub>PHZ</sub> /t <sub>PZH</sub>	GND

Vcc	Inp	outs	V <sub>M</sub>	CL	$R_L$
	Vı	t <sub>r</sub> /t <sub>f</sub>	- 141	<b>5</b> L	
1.5V±0.1V V	СС	≤2ns V	<sub>cc</sub> /2 30pF		1ΚΩ
1.8V±0.15V V	CC	≤2ns V	<sub>CC</sub> /2 30pF		1ΚΩ
2.5V±0.2V V	СС	≤2ns V	<sub>CC</sub> /2 30pF		500Ω
3.3V±0.3V 3V		≤2.5ns 1.5\		50pF	500Ω
5V±0.5V V	CC	≤2.5ns V	<sub>cc</sub> /2 50pF		500Ω



#### **Voltage Waveform Pulse Duration**



Voltage Waveform Propagation Delay Times Inverting and Non Inverting Outputs

Output
VM
Output
Waveform 1
S1 at VLOAD
(see Note B)

Output
Waveform 2
S1 at GND
(see Note B)

Output
Waveform 2
S1 at GND
(see Note B)

Voltage Waveform Enable and Disable Times
Low and High Level Enabling

Notes: A. Includes test lead and test apparatus capacitance.

- B. All pulses are supplied at pulse repetition rate ≤ 10 MHz.
- C. Inputs are measured separately one transition per measurement.
- D.  $t_{PLZ}$  and  $t_{PHZ}$  are the same as  $t_{dis.}$
- E.  $t_{PZL}$  and  $t_{PZH}$  are the same as  $t_{EN0}$
- F.  $t_{\text{PLH}}$  and  $t_{\text{PHL}}$  are the same as  $t_{\text{PD.}}$

Figure 2. Load Circuit and Voltage Waveforms



## **Ordering Information**

T4LVCE1G 125 XXX - 7

Logic Device Function Package Packing

74: Logic Prefix 125: 3-State Buffer W5: SOT25 7: Tape & Reel

LVCE: 1.4 to 5.5V

OE-Low

SE: SOT353 FZ4: DFN1410

Family

1G : One gate

Device	Package	Packaging	7" Tape and Reel	
Device	Code	Code (Note 5)	Quantity	Part Number Suffix
74LVCE1G125W5-7	W6	SOT25	3000/Tape & Reel	-7
74LVCE1G125SE-7	SE	SOT353	3000/Tape & Reel	-7
74LVCE1G125FZ4-7	FZ4	DFN1410	5000/Tape & Reel	-7

Note: 6. Pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.



## **Marking Information**

#### (1) SOT25 and SOT353

## (Top View)

5 4 XX Y W X

XX : Identification code

Y: Year 0~9

<u>W</u>: Week: A~Z: 1~26 week;

a~z: 27~52 week; z represents 52 and 53 week

52 and 53 week X : A~Z : Internal code

Part Number	Package	Identification Code
74LVCE1G125W5	SOT25	PY
7/LV/CE1G125SE	SOT353	DV

#### (2) DFN1410

### (Top View)

XX YWX XX: Identification Code

Y: Year: 0~9

 $\underline{\overline{W}}$ : Week : A~Z : 1~26 week;

a~z: 27~52 week; z represents

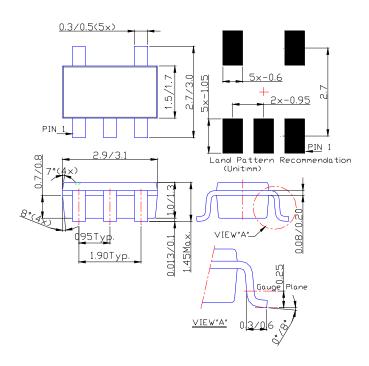
52 and 53 week X: A~Z: Internal code

Part Number	Package	Identification Code
74LVCE1G125FZ4	DFN1410	PY

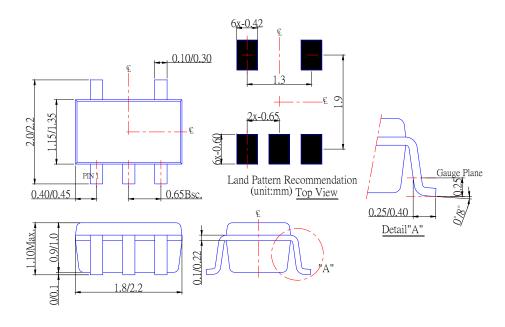


# Package Outline Dimensions (All Dimensions in mm)

### (1) Package Type: SOT25



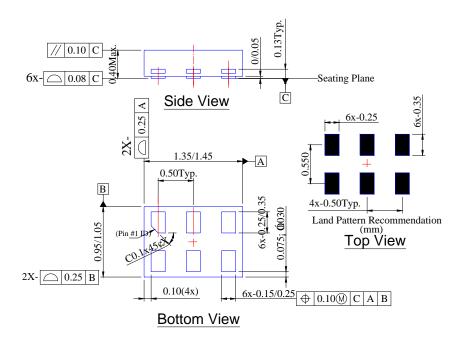
### (2) Package Type: SOT353





## Package Outline Dimensions (All Dimensions in mm)

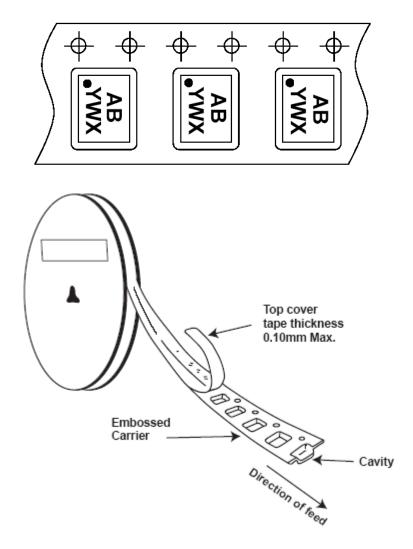
### (3) Package Type: DFN1410





## **Taping Orientation (Note 7)**

#### For DFN1410



Note: 7. The taping orientation of the other package type can be found on our website at http://www.diodes.com/datasheets/ap02007.pdf



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